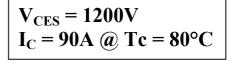
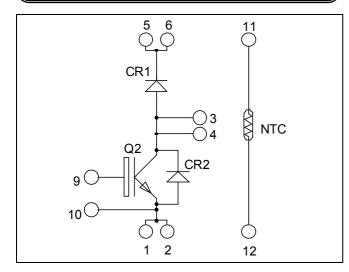
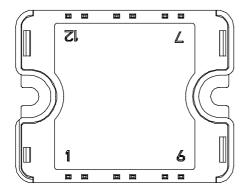


Boost chopper Trench + Field Stop IGBT4 Power module







Pins 1/2; 3/4; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- **Power Factor Correction**

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
 - Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- **RoHS** Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
T	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
$I_{\rm C}$	Continuous Conector Current	$T_c = 80$ °C	90	Α
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_c = 25^{\circ}C$	385	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	150A @ 1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.85	2.25	V
$V_{CE(sat)}$		$I_{\rm C} = 75 {\rm A}$ $T_{\rm j} = 15$	$T_{j} = 150^{\circ}C$		2.25		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3mA$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	=0V			600	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	5	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		4.4		
Coes	Output Capacitance				0.29		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			0.24		
Q_{G}	Gate charge	$V_{GE} = \pm 15V$; $V_{GE} = 15V$	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 75A$		0.57		μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		130		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			20		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 75A$			300		
T_{f}	Fall Time	$R_G = 2.2\Omega$	-		45		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Dec} = 600V$		150		ns
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$			35		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 75A$			350		
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		3.4		mJ
Lon	Turn-on Switching Energy	$V_{Bus} = 600V$	$T_J = 150$ °C		8.5		1113
E_{off}	Turn-off Switching Energy	$I_C = 75A$	$T_J = 25$ °C		4.2		mJ
	Turn on Switching Ellergy	$R_G = 2.2\Omega$	$T_J = 150$ °C		7.2		1113
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; V_{Bu} $t_p \le 10 \mu s$; $T_j = 1$			300		A

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25$ °C			250	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		90		A
V_{F}	Diode Forward Voltage	$I_{F} = 75A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.7	2.2	V
V F	Diode Forward Voltage		$T_{i} = 150^{\circ}C$		1.65		v
t_{rr}	Reverse Recovery Time	$I_F = 75A$ $V_R = 600V$ $T_j = 1500$ $T_j = 2500$	$T_j = 25$ °C		155		ns
c _{II}			$T_j = 150$ °C		300		-10
Qrr	Reverse Recovery Charge		$T_j = 25$ °C		7.3		μС
Qrr	Reverse Recovery Charge		$T_{i} = 150^{\circ}C$		15.2		μС
$\mathrm{E_{r}}$	Reverse Recovery Energy	$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$	$T_j = 25$ °C		2.6		mJ
				5.5		1113	



Thermal and package characteristics

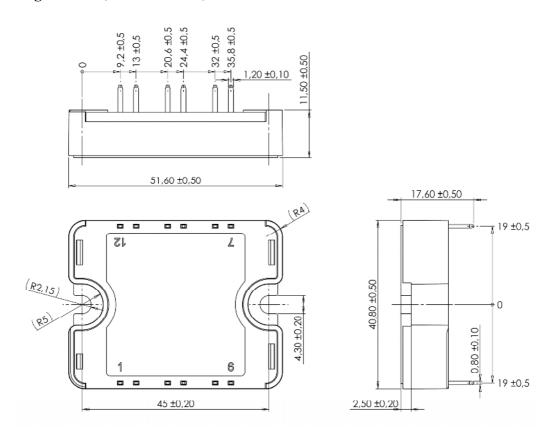
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.39	°C/W
T _{th} JC			Diode			0.62	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight		•			80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	5°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
ΔΒ/Β		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature } \\ R_T: \text{ Thermistor value at T}$$

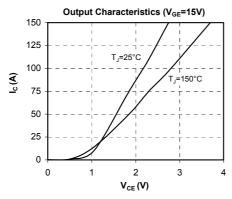
SP1 Package outline (dimensions in mm)

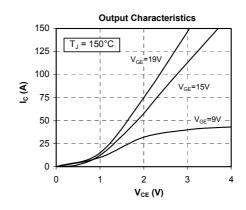


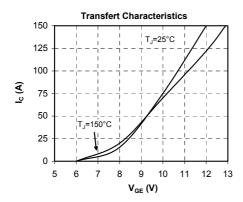
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

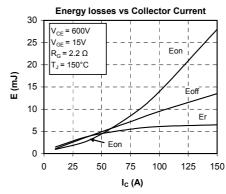


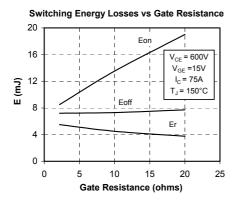
Typical Performance Curve

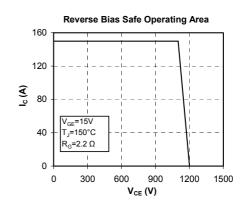


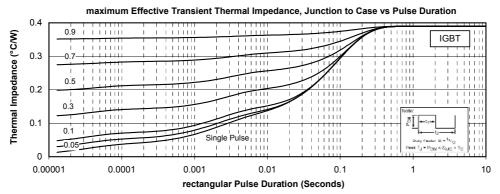




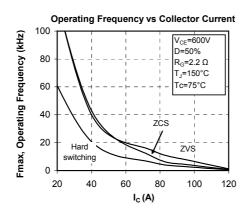


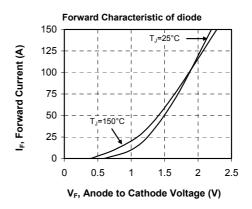


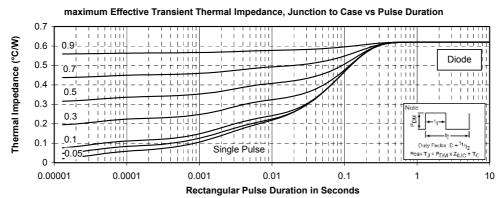












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